

NPN Silicon Transistor

# 产品规格书

批准	审 核	校 核	编制
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2018.03.02	2018.03.02	2018.03.02	2018.03.02

#### 规格书更改履历:

序号	更改内容	履历号	更改时间	责任人
1	新规制定	000	2018.03.02	郑羿

# KODENSHI AUK

**Descriptions** 

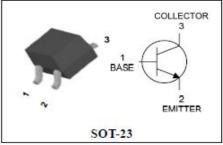
- General purpose amplifier
- High voltage application

#### **Features**

- High collector breakdown voltage:  $V_{CBO} = 180V, V_{CEO} = 160V$
- Low collector saturation voltage:  $V_{CE(sat)} = 0.5V(MAX.)$
- Complementary pair with KBT5401C

### **Ordering Information**

## **PIN Connection**



Type NO.	Marking	Package Code		
KBT5551C	<u>FNF</u> <u>□</u> • ① ②	SOT-23		

1) Device Code ② Year& Week Code Dalian

#### Absolute maximum ratings

Absolute maximum ratings			Ta=25°C
Characteristic	Symbol	Ratings	Unit
Collector-Base voltage	Vсво	180	V
Collector-Emitter voltage	Vceo	160	V
Emitter-Base voltage	Vево	6	V
Collector current	Ic	600	mA
Collector dissipation	Pc	200	mW
Junction temperature	Tj	150	Ĵ
Storage temperature	Tstg	-50~150	Ĵ

**KBT5551C** 

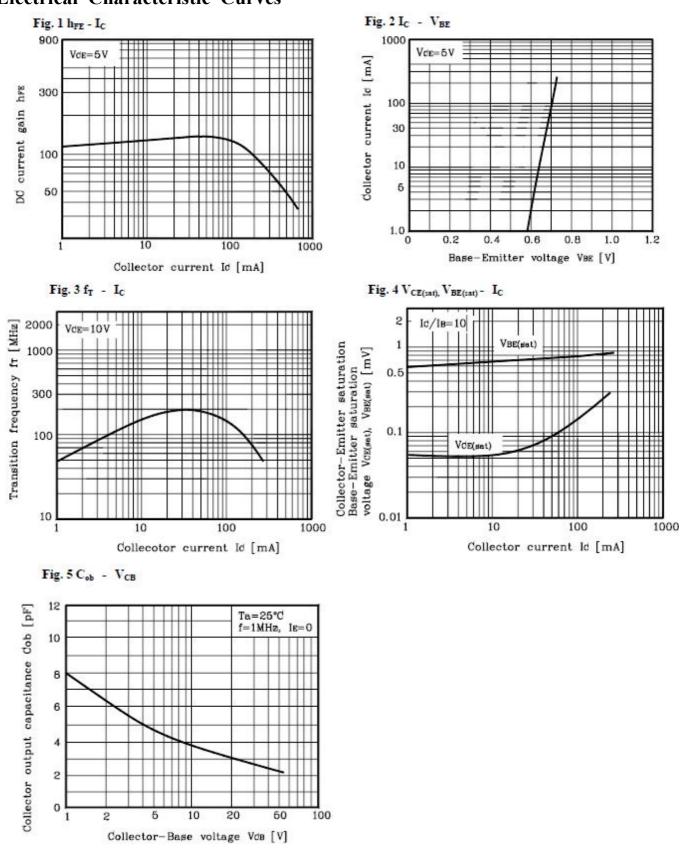
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## **Electrical Characteristics**

Ta=25 C

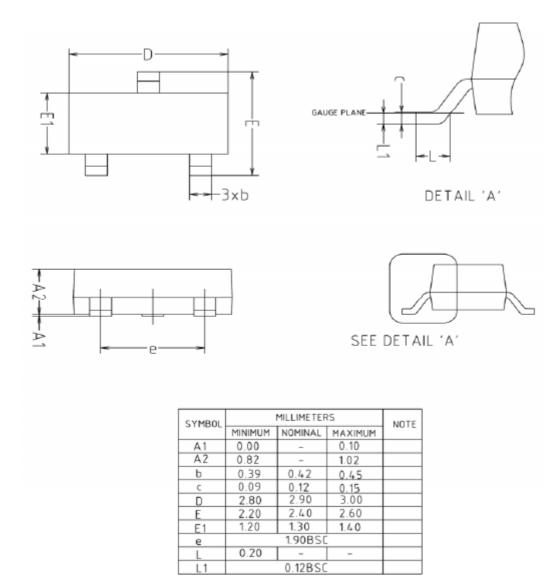
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base breakdown voltage	ВУсво	Ic=100 μ A, Iε=0	180	-	-	V
Collector-Emitter breakdown voltage	BVCEO	Ic=1mA, IB=0	160	-	-	V
Emitter-Base breakdown voltage	ВУево	IE=10 μ A, IC=0	6	-	-	V
Collector cut-off current	Ісво	V <sub>CB</sub> =120V, I <sub>E</sub> =0	-	-	50	nA
Emitter cut-off current	Іево	VEB=4V, IC=0	-	-	100	nA
DC current gain	hfe (1)	VCE=5V, IC=1mA	80	-		-
DC current gain	hfe (2)	Vce=5V, Ic=10mA	80	-	250	-
DC current gain	hfe (3)	VCE=5V, IC=50mA	30	-		-
Collector-Emitter saturation voltage	* VCE(sat)(1)	Ic=10mA, I <sub>B</sub> =1mA	-	-	0.2	V
Collector-Emitter saturation voltage	* VCE(sat)(2)	Ic=50mA, IB=5mA	-	-	0.5	V
Base-Emitter saturation voltage	* VBE(sat)(1)	Ic=10mA, IB=1mA	-	-	1	V
Base-Emitter saturation voltage	* VBE(sat)(2)	Ic=50mA, IB=5mA	-	-	1	V
Transition frequency	f⊤	VCE=10V, IC=10mA	100	-	400	MHz
Collector output capacitance	Cob	$V_{CB}=10V$ , $I_E=0$ , $f=1MHz$	-	-	6	pF

\* : Pulse Tester : Pulse Width  $\,\leq\!300\,\mu$  s, Duty Cycle  $\,\leq\!2.0\%$ 

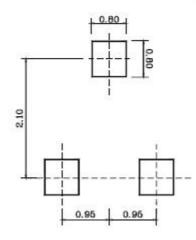


#### **Electrical Characteristic Curves**

## **Outline Dimension**



#### \*Recommend PCB solder land [Unit: mm]



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